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May 2024

FAN7711 Ballast Control Integrated Circuit

Features

- Floating Channel for Bootstrap Operation to +600V
- Low Start-up and Operating Current: 120µA, 3.2mA
- Under-Voltage Lockout with 1.8V of Hysteresis
- Adjustable Run Frequency and Preheat Time
- Internal Active ZVS Control
- Internal Protection Function (Latch Mode)
- Internal Clamping Zener Diode
- High Accuracy Oscillator
- Soft-Start Functionality

Description

The FAN7711, developed with Fairchild's unique high-voltage process, is a ballast control integrated circuit (IC) for a fluorescent lamp. FAN7711 incorporates a preheating / ignition function, controlled by an elected external capacitor, to increase lamp life. The F. 17711 detects switch operation from affigure in most through an internal active Zero-Y age Switcin (ZVS) control circuit. This control is enabled the FAN7711 to detect an open-lam, convicion without the expense of external circuit and even distribution from that the expense of external circuit and even distribution around a common-most carry and even distribution.

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S-DIP

Applications

■ Electronic Ballast

Ordering Inf ma on

Part N nb	Package	Pb-l're()	Operating Temperature Range	Packing Method
'77'	8-D;'P	7 0 7		Tube
FAN, 11N	8-SOP	Yes	-25°C ~ 125°C	Tube
N7 IMX	0-30F	CH!		Tape & Reel

Typical Application

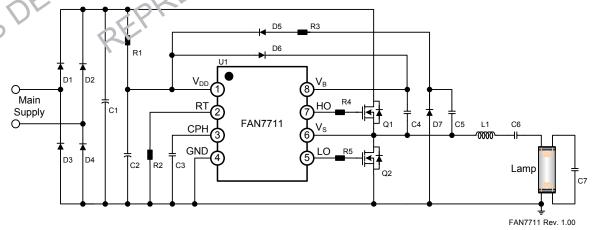


Figure 1. Typical Application Circuit for Compact Fluorescent Lamp

Internal Block Diagram

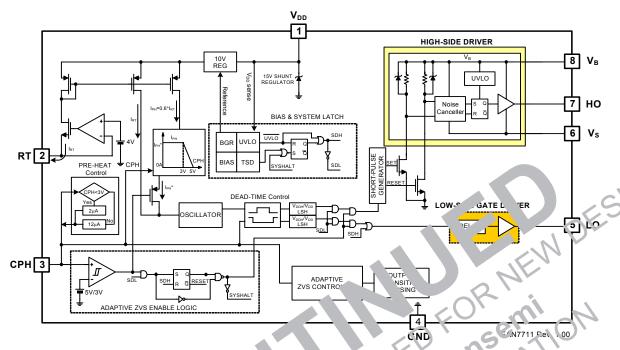


Figure 2. Inctio. Block Diagram

Pin Configuration

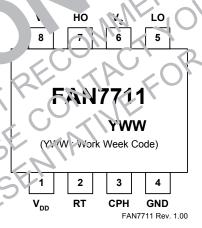


Figure 3. Pin Configuration (Top View)

Pin Definitions

Pin #	Name	Description	
1	V_{DD}	Supply voltage	
2	RT	Oscillator frequency set resistor	
3	CPH	Preheating time set capacitor	
4	GND	Ground	
5	LO	Low-side output	
6	V _S	High-side floating supply return	
7	НО	High-side output	
8	V _B	High-side floating supply	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}C$ unless otherwise specified.

Symbol	Parameter			Тур.	Max.	Unit
V _B	High-side floating supply	High-side floating supply			625	V
V _S	High-side floating supply return		-0.3		600	V
V _{IN}	RT, CPH pins input voltage		-0.3		8	V
I _{CL}	Clamping current level				25	mA
dV _S /dt	Allowable offset voltage slew rate			50		V/ns
T _A	Operating temperature range		-25		<u>``</u> 5	°C
T _{STG}	Storage temperature range				<i>i</i> 0	°C
P _D	Power dissipation	8-SOP 8-F ?		0.625	W.	W
θ_{JA}	Thermal resistance (junction-to-air)	SO ₁		100		°C/W

Note:

1. Do not supply a low-impedance voltage source to me "ternal comping Zerier cliode between the CND and the V_{DD} pin of this device.

Electrical Characteristics

 V_{BIAS} (V_{DD} , V_{BS}) = 14.0V, T_{A} = 25°C, unless otherwise specified.

Symbol	Characteristics	Conditions	Min.	Тур.	Max.	Unit
Supply Volt	age Section					
$V_{DDTH(ST+)}$	V _{DD} UVLO positive going threshold	V _{DD} increasing	12.4	13.4	14.4	
V _{DDTH(ST-)}	V _{DD} UVLO negative going threshold	V _{DD} decreasing	10.8	11.6	12.4	V
$V_{\mathrm{DDHY}(\mathrm{ST})}$	V _{DD} -side UVLO hysteresis			1.8		V
V_{CL}	Supply clamping voltage	I _{DD} =10mA	14.8	15.2		
I _{ST}	Start-up supply current	V _{DD} = 10V		120		μА
I _{DD}	Dynamic operating supply current	50kHz, C _L = 1nF		22		mA
High-Side S	supply Section (V _B -V _S)					
V _{HSTH(ST+)}	High-side UVLO positive going threshold	V _{BS} increasing	8.5	9.2	10.0	10
V _{HSTH(ST-)}	High-side UVLO negative going threshold	V _{BS} decreasing	9		9.5	У
V _{HSHY(ST)}	High-side UVLO hysteresis			0.6		
I _{HST}	High-side quiescent supply current	V _{BS} = 14V		50	7	μА
I _{HD}	High-side dynamic operating supply current	50kHz, C _L = 1	7	ZZ		mA
I _{LK}	Offset supply leakage current	V _P = V ₂ ~V	(2)	*	45	μА
Oscillator S	ection	7177) `	4/1	10	7
V _{MPH}	CPH pin preheating voltage range		2.5	3.0	3.5	V
I _{PH}	CPH pin charging current during prehea 'g		1.25	1:.00	2.85	
I _{IG}	CPH pin charging current during	V _{CPH} = 4''	8	12	16	μА
V _{MO}	CPH pin voltage level at TmL 3	IN OUT		7.0		V
f _{PRE}	Preheating frequency	R ₁ = 80kΩ, V _{DP1} = 2V	72	85	98	kHz
f _{OSC}	Running frec	$R_T = 801\Omega$	48.7	53.0	57.3	kHz
DT _{MAX}	Maximum c ad time	V _{CFH} = 1V, V _S = GND during reneat mode		3.1		μS
DT _{MIN}	ad time	$V_{CCH} = 6V' V_S = GND$ during run moa :		1.0		μS
O' Sec	TO SOR	//				
I _{OH+}	h-side driver sourcing current	PW = 10μs	250	350		
JH-	High-side driver sinking current	PW = 10μs	500	650		A
10_+	Laviside driver sourcing current	PW = 10μs	250	350		mA
I _{OL} -	ow-side driver sink currout	PW = 10μs	500	650		
l _I IOP	High-side driver 'urı-cn rising time	C _L = 1nF, V _{BS} = 15V		45		
S t _{HOL}	High-side driver furn-off rising time	C _L = 1nF, V _{BS} = 15V		25		
t _{LOR}	Low-side driver turn-on rising time	ow-side criver turn-on rising time $C_L = 1nF$, $V_{BS} = 15V$ 45			ns	
t _{LOL}	Low-side driver turn-off rising time $C_L = 1nF, V_{BS} = 15V$			25		
V _S ⁽²⁾	Maximum allowable negative V _S swing range for signal propagation to high-side output			-9.8		V
Protection S	Section			•		
V _{CPHSD}	Shutdown voltage	// = 0 offer run made	2.6			V
I _{SD}	Shutdown current	V _{RT} = 0 after run mode		250	450	μА
TSD	Thermal shutdown ⁽²⁾			165		°C

Note:

2. This parameter, although guaranteed, is not 100% tested in production.

Typical Characteristics

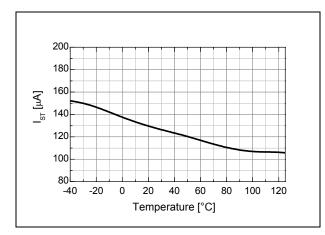
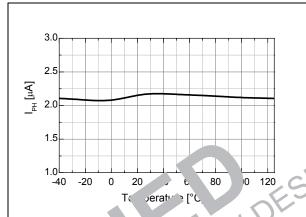
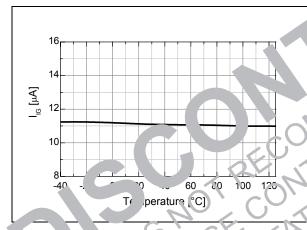


Figure 4. Start-Up Current vs. Temp.



Figur 5. Pre Jurrent vs Temp.



jure 6. Ignition Current vs. Temp

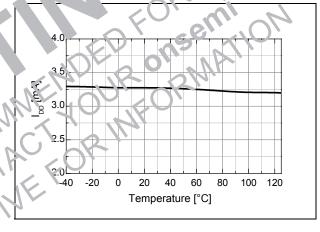


Figure 7. Operating Current vs. Temp.

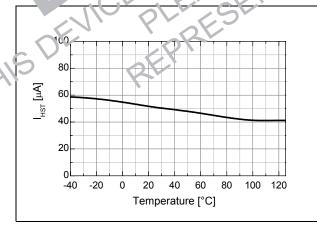


Figure 8. Start-Up Current vs. Temp.

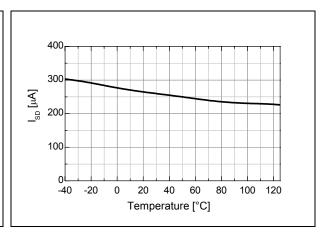


Figure 9. Shutdown Current vs. Temp.

Typical Characteristics (Continued)

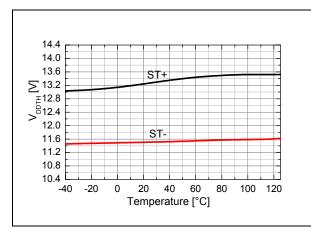
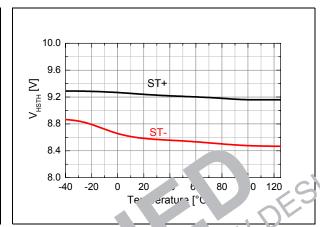


Figure 10. V_{DD} UVLO vs. Temp.



F ure 1: 'BS _O vs. Temp.

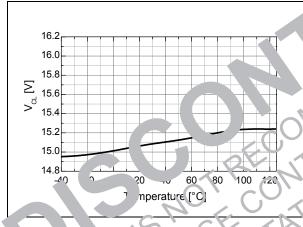


Fig e 1∠. V_{DD} Clamp Voltage s. Temp.

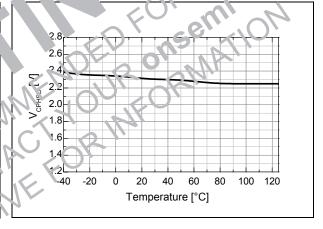


Figure 13. Shutdown Voltage vs. Temp.

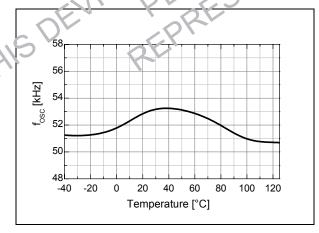


Figure 14. Running Frequency vs. Temp.

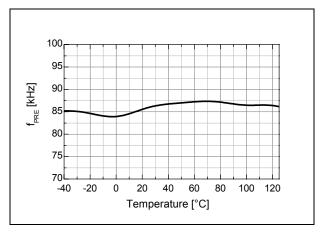
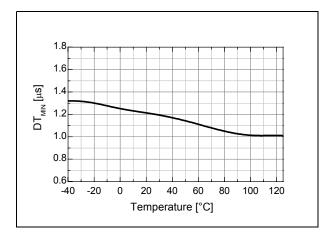


Figure 15. Preheating Frequency vs. Temp.

Typical Characteristics (Continued)



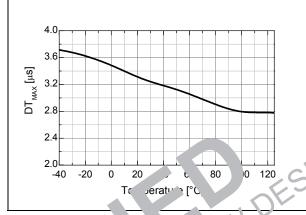


Figure 16. Minimum Dead Time vs. Temp.

Figure 7. Max nun ad Time vs. Temp.

Typical Application Information

1. Under-Voltage Lockout (UVLO) Function

The FAN7711 has UVLO circuits for both high-side and low-side circuits. When V_{DD} reaches $V_{DDTH(ST+)}$, UVLO is released and the FAN7711 operates normally. At UVLO condition, FAN7711 consumes little current, noted I_{ST} . Once UVLO is released, FAN7711 operates normally until V_{DD} goes below $V_{DDTH(ST-)}$, the UVLO hysteresis. At UVLO condition, all latches that determine the status of the IC are reset. When the IC is in the shutdown mode, the IC can restart by lowering V_{DD} below $V_{DDTH(ST-)}$.

FAN7711 has a high-side gate driver circuit. The supply for the high-side driver is applied between V_B and V_S . To protect the malfunction of the driver at low supply voltage, between V_B and V_S , FAN7711 provides an additional UVLO circuit between the supply rails. If V_B - V_S is under $V_{HSTH(ST+)}$, the driver holds low-state to turn off the high-side switch, as shown in Figure 18. As long as V_B - V_S is higher than $V_{HSTH(ST-)}$ after V_B - V_S exceeds $V_{HSTH(ST+)}$, operation of the driver continues.

2. Oscillator

The ballast circuit for a fluorescent lamp is base. In the LCC resonant tank and a half-bridge invession of the shown in Figure 18. To accomplish a rose in the Switching (ZVS) of the half-bridge investing the cuit, the LCC is driven at a higher frequency that its a sonant frequency, which is determed to L. C. C. C. and R. where R. is the equivalent lamp's improvince

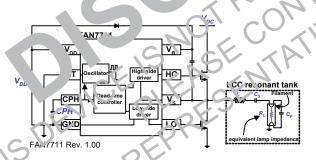


Figure 18. Resonant Inverter Circuit Based on LCC Resonant Tank

The transfer function of LCC resonant tank is heavily dependent on the lamp impedance, R_L , as illustrated in Figure 19. The oscillator in FAN7711 generates effective driving frequencies to assist lamp ignition and improve lamp life longevity. Accordingly, the oscillation frequency is changed in the following sequence:

Preheating freq.->Ignition freq.-> Normal running freq.

Before the lamp is ignited, the lamp impedance is very high. Once the lamp is turned on, the lamp impedance significantly decreases. Since the resonant peak is very high due to the high-resistance of the lamp at the instant of turning on the lamp, the lamp must be driven at higher frequency than the resonant frequency, shown as (A) in Figure 19. In this mode, the current supplied by the inverter mainly flows through C_P . C_P connects both filaments and makes the current path to ground. As a result, the current warms up the filament for easy ignition. The amount of the current can be adjusted by controlling the oscillation frequency changing the capacitance of C_P . The driving a quency f_{PRE} , is called preheating frequency and duerive by:

$$f_{PRE} = 6 \times (EQ 1)$$

Ifter the rm-up, the FAN7711 decreases the nue v, shown as (B) of Figure 19. This action includes the voltage of the ramp and helps the fluor cent lamp ignite. The ignition frequency is described as a function in CPH voltage, as follows:

$$f_G = \left[0.3 \times (5 - V_{CLL}) + 1\right] \times f_{OSC}$$
 (EQ 2)

where V_{CPH} is the voltage of CPH capacitor.

Equatior 2 is valid only when V_{CPH} is between 3V to 5V before FAN7711 enters running mode. Once V_{CPH} reaches 5V, the internal latch records the exit from ignition mode. Unless V_{DD} is below $V_{DDTH(ST-)}$, the preheating and ignition modes appear only once during lamp start transition.

Finally, the lamp is driven at a fixed frequency by an external resistor, R_T , shown as (C) of Figure 19. If V_{DD} is higher than $V_{DDTH(ST+)}$ and UVLO is released, the voltage of R_T pin is regulated to 4V. This voltage adjusts the oscillator's control current according to the resistance of R_T . Because this current and an internal capacitor set the oscillation frequency, the FAN7711 does not need any external capacitors.

The proposed oscillation characteristic is given by:

$$f_{OSC} = \frac{4 \times 10^9}{RT}$$
 (EQ 3)

Even in the active ZVS mode, shown as (D) in Figure 19, the oscillation frequency is not changed. The dead-time is varied according to the resonant tank characteristic.

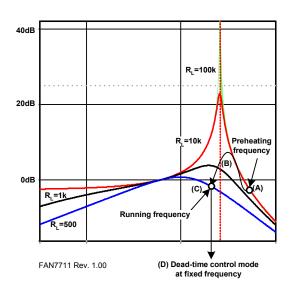
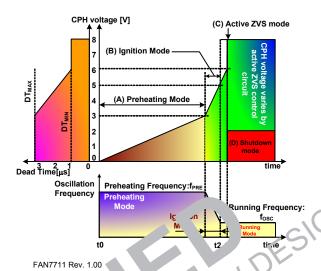


Figure 19. LCC Transfer Function in Terms of Lamp Impedance

3. Operation Modes

FAN7711 has four operation modes: (A) pre ating mode, (B) ignition mode, (C) active ZVS r and (D) shutdown mode, depicted in Figure 20 The no. automatically selected by the volt ,e or 7H apacitor, shown in Figure 20. In modes (A) nd (B), e C H actor as a timer to determine the least and linear nition times. After the preheating an ignition me ine role of the CPH is changed to smilize to active 21/3 control circuit. In this node, the last time of the inverter is selected high the good of CPH. Only when FAN7/11 is in active Z ? mode is possible to shut of the whole sy Jun ing 'Program Pulling the CPH pin below 2V in ive Z in de, causes the FAN7711 to enter sh down lode. In shutdown mode, all active operation is sum a, except UVLO and some bias arcuitry. The shutdown mode is triggered by the external CPH control or the active ZVS circuit. The active ZVS circuit automatically detects larup removal (open-lamp rendition) and decreases CPH voltage below 2V to protect the inverter switches from damage.



igure O. r., on Modes

3.1 hea g h. (c0~t1)

her. I_{DD} eeds $V_{\rm DDTH(ST+)}$, the FAN7711 starts of atic. At this time, an interred current source (I_{PH}) char, s CPH. CPH voltage increases from UV to 3V in preheating needs. Accordingly, the oscillation frequency rollows the Equation 4. In this mode, the lamp is not ignited but warmed up for besy ignition. The preheating time depends on the size of CPH:

$$f_{p, \text{ pheat}} = \frac{3 \times CPH}{I_{PH}}$$
 [Sec.] (EQ 4)

According to preheating process, the voltage across the lamp to ignite is reduced and the lifetime of the lamp is increased. In this mode, the dead time is fixed at its maximum value.

3.2 Ignition Mode (t1~t2)

When the CPH voltage exceeds 3V, the internal current source to charge CPH is increased about six times larger than I_{PH} , noted as I_{IG} , causing rapid increase in CPH voltage. The internal oscillator decreases the oscillation frequency from f_{PRE} to f_{OSC} as CPH voltage increases. As depicted in Figure 20, lowering the frequency increases the voltage across the lamp. Finally, the lamp ignites. Ignition mode is defined when CPH voltage lies between 3V and 5V. Once CPH voltage reaches 5V, the FAN7711 does not return to ignition mode, even if the CPH voltage is in that range, until the FAN7711 restarts from below $V_{DDTH(ST-)}$. Since the ignition mode continues when CPH is from 3V to 5V, the ignition time is given by:

$$t_{ignition} = \frac{2 \times CPH}{I_{IG}}$$
 [Sec.] (EQ 5)

In this mode, dead time varies according to the CPH voltage.

3.3 Running and Active Zero-Voltage Switching (AZVS) Modes (t2~)

When CPH voltage exceeds 5V, the operating frequency is fixed to f_{OSC} by R_T. However, active ZVS operation is not activated until CPH reaches ~6V. The FAN7711 prepares for active ZVS operation from the instant CPH exceeds 5V during t2 to t3. When CPH becomes higher than ~6V at t3, the active ZVS operation is activated. To determine the switching condition, FAN7711 detects the transition time of the output (V_S pin) of the inverter by using VB pin. From the output-transition information, FAN7711 controls the dead time to meet the ZVS condition. If ZVS is satisfied, the FAN7711 slightly increases the CPH voltage to reduce the dead time and to find optimal dead time, which increases the efficiency and decreases the thermal dissipation and EMI of the inverter switches. If ZVS fails, the FAN7711 decreases CPH voltage to increase the dead time. CPH voltage is adjusted to meet optimal ZVS operation. During the active ZVS mode, the amount of the charging/ discharging current is the same as I_{PH}. Figure 21 depicts normal operation waveforms.

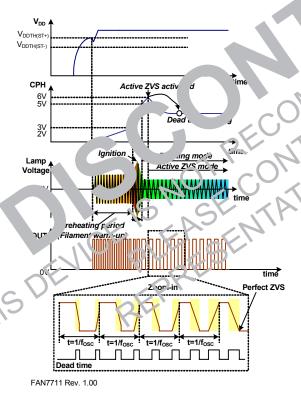


Figure 21. Typical Transient Waveform from Preheating to Active ZVS Mode

3.4 Shutdown Mode

If the voltage of capacitor CPH is decreased below $\sim 2.6 \text{V}$ by an external application circuit or internal protection circuit, the IC enters shutdown mode. Once the IC enters shutdown mode, this status continues until an internal latch is reset by decreasing V_{DD} below $V_{DDTH(ST-)}$. Figure 22 shows an example of external shutdown control circuit.

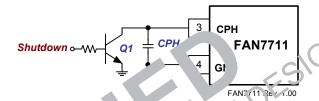


Figure 22. E. ern Chatdown Chicuit

The property of the Card charging current is the same as a possible to shut off the IC using small signal ansistor FAN7711 are rides active ZVS ope. From the ling the Card time according to the voltage of CPH. If ZVS fails even at the maximum dead time, FAN7711 stops driving the inverter.

The FAN7711 thermal shudown circuit senses the lanction emperature of the IC. If the temperature exceeds 160°C, the thermal shutdown circuit stops operation of the FAN7711.

The curren usages of shutdown mode and undervoltage lockout status are different. In shutdown mode, some circuit blocks, such as bias circuits, are kept alive. Therefore, the current consumption is slightly higher than during under-voltage lockout.

4. Automatic Open-Lamp Detection

FAN7711 can automatically detect the open-lamp condition. When the lamp is opened, the resonant tank fails to make a closed-loop to the ground, as shown in Figure 23. The supplied current from the $V_{\rm S}$ pin is used to charge and discharge the charge pump capacitor, $C_{\rm P}$. Since the open-lamp condition means resonant tank absence, it is impossible to meet ZVS condition. In this condition, the power dissipation of the FAN7711, due to capacitive load drive, is estimated as:

$$P_{Dissipation} = \frac{1}{2} \times C_P \times V_{DC}^2 \times f \quad [W]$$
 (EQ 6)

where f is driving frequency and V_{DC} is DC-link voltage.

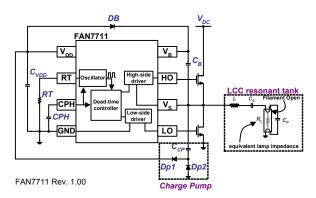


Figure 23. Current Flow When the Lamp is Open

Assuming that C_P , V_{DC} , and f are 1nF, 311V, and 50kHz, respectively; the power dissipation reaches about 2.4W and the temperature of FAN7711 is increased rapidly. If no protection is provided, the IC can be damaged by the thermal attack. Note that hard-switching condition during the capacitive-load drive causes lots of EMI.

Figure 24 illustrates the waveforms during the operamp condition. In this condition, the charging and discharging current of C_P is directly determined by FAN7711 and considered hard-switching controls. The FAN7711 tries to meet ZVS conditions by Facing CPH voltage to increase dead time of ZVL fails and CPH goes below 2V, even though the lead time realness its maximum value, FAN77 and of the D to protect against damage. To relate that FAN77 and the Delow $V_{DDTH(S^T)}$ less an internal latch circuit, which remembers the status of the

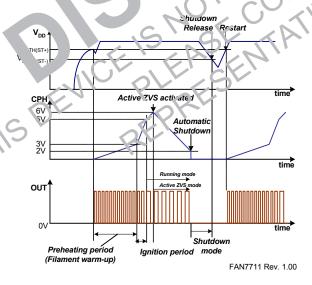


Figure 24. CPH Voltage Variation in Open-Lamp Condition

5. Power Supply

When V_{DD} is lower than $V_{DDTH(ST+)}$, it consumes very little current, I_{ST} , making it possible to supply current to the V_{DD} pin using a resistor with high resistance (R_{start} in Figure 25). Once UVLO is released, the current consumption is increased and whole circuits are operated, which requires additional power supply for stable operation. The supply must deliver at least several mA. A charge pump circuit is a cost-effective method to create an additional power supply and allows C_P to be used to reduce the EMI.

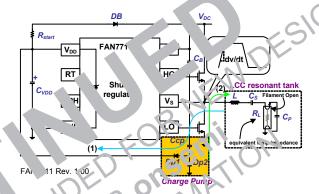


Figure 25. Local Fower Supply for V_{DD} Using a Charge Pump Circuit

As presented in Figure 25, when V_S is high, the inductor current and C_{CP} create an output transition with the slope of dv/ct. The rising edge of V_S charges C_{CP} At that time, the current that flows through C_{CP} is:

$$I \cong C_{CP} \times \frac{dv}{dt}$$
 (EQ 7)

This current flows along the path (1). It charges C_{VDD} , which is a bypass capacitor to reduce the noise on the supply rail. If C_{VDD} is charged over the threshold voltage of the internal shunt regulator, the shunt regulator is turned on and regulates V_{DD} with the trigger voltage.

When V_S is changing from high to low state, C_{CP} is discharged through Dp2, shown as path (2) in Figure 26. These charging/discharging operations are continued until FAN7711 is halted by shutdown operation. The charging current, I, must be large enough to supply the operating current of FAN7711.

The supply for the high-side gate driver is provided by the boot-strap technique, as illustrated in Figure 26. When the low-side MOSFET connected between V_S and GND pins is turned on, the charging current for V_B flows through D_B . Every low V_S gives the chance to charge the C_B . Therefore C_B voltage builds up only when FAN7711 operates normally.

When ${\rm V_S}$ goes high, the diode ${\rm D_B}$ is reverse-biased and ${\rm C_B}$ supplies the current to the high-side driver. At this time, since ${\rm C_B}$ discharges, ${\rm V_{B^{-}}V_{S}}$ voltage decreases. If ${\rm V_{B^{-}}V_{S}}$ goes below ${\rm V_{HSTH(ST^{-})}}$, the high-side driver cannot operate due to the high-side UVLO protection circuit. ${\rm C_B}$ must be chosen to be large enough not to fall into UVLO range due to the discharge during a half of the oscillation period, especially when the high-side MOSFET is turned on.

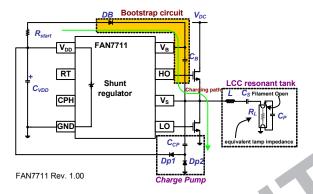


Figure 26. Implementation of Floating Power S pply
Using the Bootstrap Method

Design Guide

1. Start-up Circuit

The start-up current (I_{ST}) is supplied to the IC through the start-up resistor, R_{start} . Once operation starts, the power is supplied by the charge pump circuit. To reduce the power dissipation in R_{start} , select R_{start} as high as possible, considering the current requirements at start-up. For $220V_{AC}$ power, the rectified voltage by the full-wave rectifier makes DC voltage, as shown in Equation 8. The voltage contains lots of AC component due to poor regulation characteristic of the simple full-wave rectifier:

$$V_{DC} = \sqrt{2} \times 220[V] \cong 311[V]$$
 (EQ 8)

Considering the selected parameters, R_{start} must satisfy the following equation:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{R_{start}} > I_{ST}$$
 (EQ 9)

From Equation 9, R_{start} is selected as:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{I_{ST}} > R_{start}$$
 (EC)

Note that if choosing the maximum R_{start} takes and time for V_{DD} to reach $V_{DDTH(st+)}$. Considering V_{DD} at time, R_{start} must be selected as shown in the run 30.

Another important concerns runosing R_{start} is the available power rating R_{start} . To a commercially available, low-consisted R_{start} must obey the following rule:

$$\frac{(V_{\text{DC}} - V_{\text{Coll}})^2}{v_{\text{coll}}} < \frac{1}{4} - |W|$$
 (EQ 11)

A uming V_{DC} =311V and V_{CL} =15V the minimum results of R_{start} is about 35 Jk Ω .

When the IC operates in shutdown mode due to thermal protection, open-lamp protection, or hard-switching protection, the IC consumes shutdown current, I_{SD} , which is larger than I_{S1} To prevent restart during this mode, R_{start} must be selected to cover I_{SD} current consumption. The following equation must be satisfied:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{I_{SD}} > R_{start}$$
 (EQ 12)

From Equations 10 - 12; it is possible to select R_{start}:

(1) For safe start-up without restart in shutdown mode:

$$4(V_{DC} - V_{CL})^2 < R_{start} < \frac{V_{DC} - V_{DDTH(ST+)}}{I_{SD}}$$
 (EQ 13)

(2) For safe start-up with restart from shutdown mode:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{I_{SD}} < R_{start} < \frac{V_{DC} - V_{DDTH(ST+)}}{I_{ST}}$$
 (EQ 14)

If R_{start} meets Equation 14, restart operation is possible. However, it is not recommended to choose R_{start} at that range because V_{DD} rising time could be long and it increases the lamp's turn-on delay time, as depicted in Figure 27.

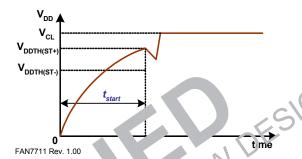


Figure 7. Lan Build-up

Figure 28 how the equivalent circuit for estimating than circuit analysis, V_{DD} variation versus time nive by:

$$V_{DD}(t) = (V_{DC} - R_{start} \cdot I_{ST}) \left(e^{-I/(R_{start} \cdot C_{VDL})} \right)$$
 (EQ 15)

where C_{1DD} is the total capacitance of the bypass capacitors connected between V_{DD} and GND.

From Equation 15, it is possible to calculate t_{start} by substituting $V_{DD(t)}$, with $V_{DDTH(ST+)}$:

$$t_{start} = -R_{st,rt} \cdot C_{VDD} \cdot \ln \frac{V_{DC} - R_{start} \cdot I_{ST} - V_{DDTH(ST+)}}{V_{DD} - R_{start} \cdot I_{ST}} \quad (EQ 16)$$

In general, Equation 16 can be simplified as:

$$t_{start} \approx \frac{R_{start} \cdot C_{VDD} \cdot V_{DDTH(ST+)}}{V_{DC} - R_{start} \cdot I_{ST} - V_{DDTH(ST+)}}$$
(EQ 17)

Accordingly, t_{start} can be controlled by adjusting the value of R_{start} and C_{VDD} . For example, if V_{DC} =311V, R_{start} =560k, C_{VDD} =10 μ F, I_{st} =120 μ A, and $V_{DDTH(ST+)}$ =13.5V, t_{start} is about 0.33s.

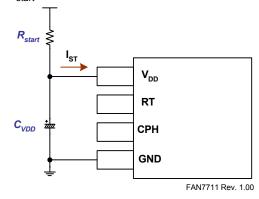


Figure 28. Equivalent Circuit During Start

2. Current Supplied by Charge Pump

For the IC supply, the charge pump method is used in Figure 29. Since C_{CP} is connected to the half-bridge output, the supplied current by C_{CP} to the IC is determined by the output voltage of the half-bridge.

When the half-bridge output shows rising slope, C_{CP} is charged and the charging current is supplied to the IC. The current can be estimated as:

$$I = C_{CP} \frac{dV}{dt} \approx C_{CP} \frac{V_{DC}}{DT}$$
 (EQ 18)

where DT is the dead time and dV/dt is the voltage variation of the half-bridge output.

When the half-bridge shows falling slope, C_{CP} is discharged through Dp2. Total supplied current, I_{total} , to the IC during switching period, t, is:

$$I_{total} = I \cdot DT = C_{CP} \cdot V_{DC}$$
 (EQ 19)

From Equation 19, the average current, I_{avg} , supplied to the IC is obtained by:

$$I_{avg} = \frac{I_{total}}{t} = \frac{C_{CP} \cdot V_{DC}}{t} = C_{CP} \cdot V_{DC} \cdot f$$

For the stable operation, I must be his er than the required current. If I avg is deeds the shunt regulator implemented in the chip which can cause unwanted heat generation. Fore, C_{CC} must be selected considering table operation and thermal generation.

exame e, rep=0.5nf- V_{DC}=311V, and f=50kHz, ravg is 7.8mA is enough current for stable operation.

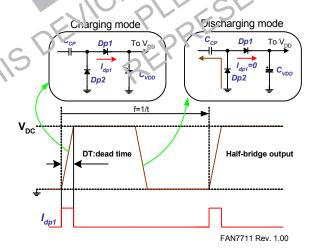


Figure 29. Charge Pump Operation

3. Lamp Turn-on Time

The turn-on time of the lamp is determined by supply build-up time t_{start} , preheating time, and ignition time; where t_{start} has been obtained by Equation 17. When the IC's supply voltage exceeds $V_{DDTH(ST+)}$ after turn-on or restart, the IC operates in preheating mode. This operation continues until CPH pin's voltage reaches ~3V. In this mode, CPH capacitor is charged by I_{PH} current, as depicted in Figure 30. The preheating time is achieved by calculating:

$$t_{preheat} = 3 \frac{CPH}{I_{Ph}}$$
 (EQ 21)

The preheating time is all ad to it in life (especially filament); therefore, he charact stics of a given lamp should be confidence there woosing the time.

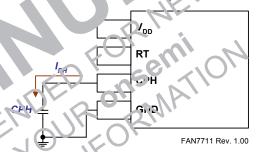


Figure 30. Preheating Timer

Compared to the preheating time, it is almost impossible to exactly predict the ignition time, whose definition is the time from the end of the preheating time to ignition. In general, the lamp ignites during the ignition mode. Therefore, assume that the maximum ignition time is the same as the duration of ignition mode, from 3V until CPH reaches 5V. Thus, ignition time can be defined as:

$$t_{ignition} = (5-3)\frac{CPH}{I_{IG}} = 2\frac{CPH}{I_{IG}}$$
 (EQ 22)

Note that, at ignition mode, CPH is charged by I_{IG} , which is six times larger than I_{PH} . Consequently, total turn-on time is approximately:

VDD Build-Time + Preheating Time + Ignition Time =

$$t_{ignition} = (5-3)\frac{CPH}{I_{IG}} = 2\frac{CPH}{I_{IG}}$$
 [Sec.] (EQ 23)

4. PCB Guideline

Component selection and placement on PCB is important when using power control ICs. Bypass the V_{CC} to GND as close to the IC terminals as possible with a low-ESR/ESL capacitor, as shown in Figure 31. This bypassed capacitor (C_{BP}) can reduce the noise from the power supply parts, such as start-up resistor and charge pump.

The signal GND must be separated from the power GND. So, the signal GND should be directly connected to the rectify capacitor using an individual PCB trace.

In addition, the ground return path of the timing components (C_{PH} , R_{T}) and V_{DD} decoupling capacitor should be connected directly to the IC GND lead and not via separate traces or jumpers to other ground traces on the board. These connection techniques prevent high-current ground loops from interfering with sensitive timing component operations and allow the control circuit to reduce common-mode noise due to output switching.

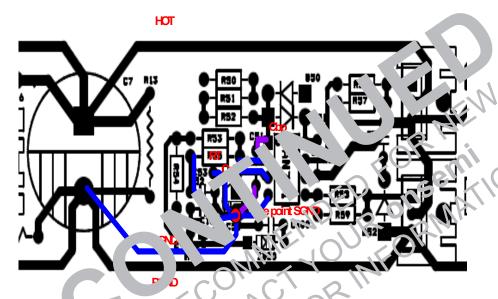
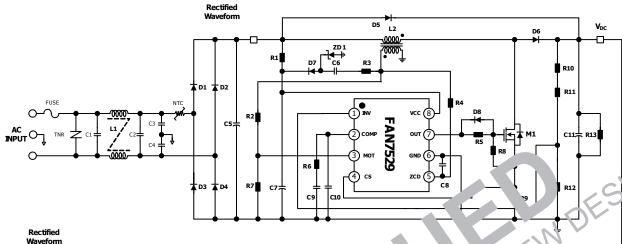


Figure 31 Prefigating Times

Typical Application Diagram



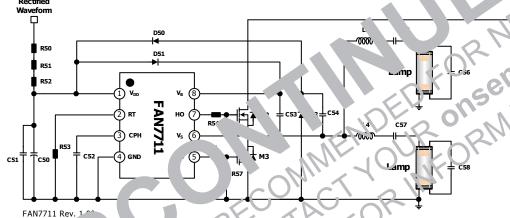


Figure 32. Application Circuit of J2W Two Lamps

Component List for 32W Two Lamps

Part	Value	Note	Part	Value	Note
Resisto		r	C55	15nF/630V	Miller Capacitor
R1	330kΩ 1/2W		C56	2.7nF/1kV	Miller Capacitor
R2	750kΩ	1/4W	C57	15nF/630V	Miller Capacitor
R3	100Ω	1/2W	C58	2.7nF/1kV	Miller Capacitor
R4	20kΩ	1/4W		Diode)
R5	47Ω	1/4W	D1	1N4007	1kV,1A
R6	10kΩ	1/4W	D2	1N4007	1kV,1A
R7	50kΩ	1/4W	D3	1N4007	¹kV,1A
R8	47kΩ	1/4W	D4	1N4007	i /,1A
R9	0.3Ω	1W	D5	UF400	tra ust,1k1A
R10	1ΜΩ	1/4W	D6	UF 707	Ulura Fast, !k1A
R11	1ΜΩ	1/4W	D7	1N4'1 3	100V,1A
R12	12.6kΩ	1/4W,1%	D8	N414	100V,1A
R13	220kΩ	2W	D.	Ur-1007	Ultra Fast,1kV,1A
R50	150kΩ	1/4W	51	UF4007	Utro Fast.1NV3A
R51	150kΩ	1/4W		JF4007	Ultra Fast.1kV,1A
R52	150kΩ	1/4W	ZD1	IN4746A	Zener 18V, 1W
R53	90kΩ 1/ 1/		MOSFET		
R54	10Ω	1/4		FQPF5N60C	500V,6A
R55	47Ω	4W	M2	FQPF5N50C	500V,5A
R56	47kΩ	./4W	î/J3	FQPF5N50C	500V,5A
R57	47Ω	1/4///		Fuse	
R58	47kQ	1/4W	Fuse	3A/250V	
	apacito			TNR	
01	471	Pux Capacitor	TNR	471	
C2	1.J0nF/275V _{AC}	BDX Capacitor			
3	220UpF/3kV	Cerartic Capacitor		NTC	
C4	22u0pF/3kV	Cerarnic Capacitor	NTC	10D-09	
C5	0.22µF/630V	Miller Capacitor		Line Filt	ter
CG	12nF/50∀	Ceramic Capacitor	LF1	40mH	
C7	22µF/5ύ∀	Electrolytic Capacitor		Transfor	mer
C8	39pF/50V	Ceramic Capacitor	L1	0.94mH(75T:10T)	El2820
C9	1μF/50V	Ceramic Capacitor	Inductor		or
C10	0.1µF/50V	Ceramic Capacitor	L2	3.2mH(130T)	El2820
C11	47μF/450V	Electrolytic Capacitor	L3	3.2mH(130T)	El2820
C50	10μF/50V	Electrolytic Capacitor		IC	
C51	1μF/50V	Ceramic Capacitor	U1	FAN7711	Fairchild Semiconductor
C52	0.47µF/25V	Ceramic Capacitor,5%	U2	FAN7529	Fairchild Semiconductor
C53	100nF/50V	Ceramic Capacitor			
C54	470pF/1kV	Ceramic Capacitor			

Component List for 20W CFL

Part	Value	Note	Part	Value	Note
	Resistor			Diode	
R1	470kΩ	1/4W	D1	D1 1N4007 1kV/1A	
R2	90kΩ	1/4W	D2	1N4007	1kV/1A
R3	10Ω	1/4W	D3	1N4007	1kV/1A
R4	47Ω	1/4W	D4	1N4007	1kV/1A
R5	47Ω	1/4W	D5	UF4007	1kV/1A,Ultra Fast
			D6	UF4007	1'1A,Ultra Fast
	Capacitor		D7	UF4007	1kV/1 Ultra Fast
C1	22µF/250V	Electrolytic Capacitor	Ir actor		
C2	10μF/50V	Electrolytic Capacitor	L1	2.5m ^L (28 [¬])	E16.6S
C3	470nF/25V	Miller Capacitor		MC 7F	
C4	100nF/25V	Miller Capacitor	Q1	PF1N. C	500V,1A
C5	470pF/630V	Miller Capacitor	C	FQ1 .50C	500V,1A
C6	33nF/630V	Miller Capacitor		IC	M-1/m
C7	3.3nF/1kV	Miller Capacite		FAN7711	Carchild Semiconductor

Note:

3. Refer to the typical application circuit production in igure 1.

Package Dimensions

8-SOP

Dimensions are in millimeters unless otherwise noted.

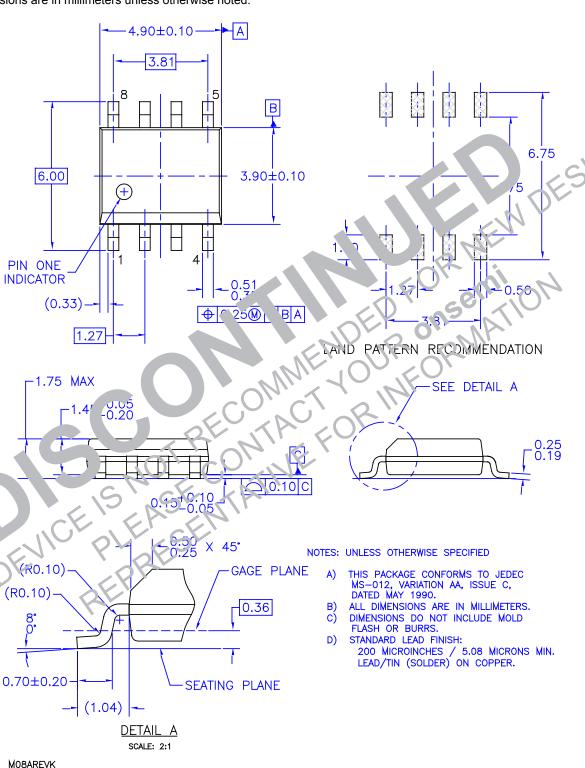
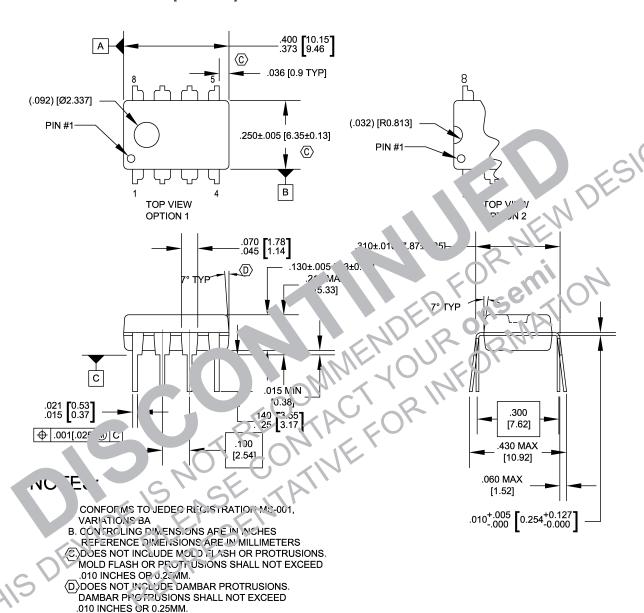


Figure 33. 8-Lead Small Outline Package (SOP)

Package Dimensions

8-DIP

Dimensions are in inches and [millimeters] unless otherwise noted.



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Figure 34. 8-Lead Dual In-Line Package (DIP)





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